

Silizium-PIN-Fotodiode mit Tageslichtsperrfilter Silicon-PIN-Photodiode with Daylight Filter

SFH 205 FA



Wesentliche Merkmale

- Speziell geeignet für Anwendungen bei 880 nm
- Kurze Schaltzeit (typ. 20 ns)
- 5 mm-Plastikbauform im LED-Gehäuse
- Auch gegurtet lieferbar

Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern, Gerätefernsteuerungen
- Lichtschranken für Gleich- und Wechsellichtbetrieb

Features

- Especially suitable for applications of 880 nm
- Short switching time (typ. 20 ns)
- 5 mm LED plastic package
- Also available on tape and reel

Applications

- IR-remote control of hi-fi and TV sets, video tape recorders, dimmers, remote control of various equipment
- Photointerrupters

Typ Type	Bestellnummer Ordering Code
SFH 205 FA	Q62702-P1677

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Löttemperatur (Lötstelle 2 mm vom Gehäuse entfernt bei Lötzeit $t \leq 3$ s) Soldering temperature in 2 mm distance from case bottom ($t \leq 3$ s)	T_S	230	°C
Sperrspannung Reverse voltage	V_R	32	V
Verlustleistung, $T_A = 25$ °C Power dissipation	P_{tot}	150	mW

Kennwerte ($T_A = 25$ °C, $\lambda = 870$ nm)
Characteristics

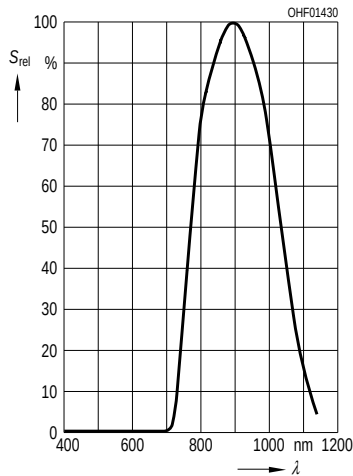
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Fotostrom Photocurrent $V_R = 5$ V, $E_e = 1$ mW/cm ²	I_P	60 (≥ 45)	µA
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\ max}$	900	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{max} Spectral range of sensitivity $S = 10\%$ of S_{max}	λ	740 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	7.00	mm ²
Abmessungen der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	2.65×2.65	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip surface to case surface	H	2.3 ... 2.5	mm
Halbwinkel Half angle	φ	± 60	Grad deg.
Dunkelstrom, $V_R = 10$ V Dark current	I_R	2 (≤ 30)	nA

Kennwerte ($T_A = 25\text{ °C}$, $\lambda = 870\text{ nm}$)

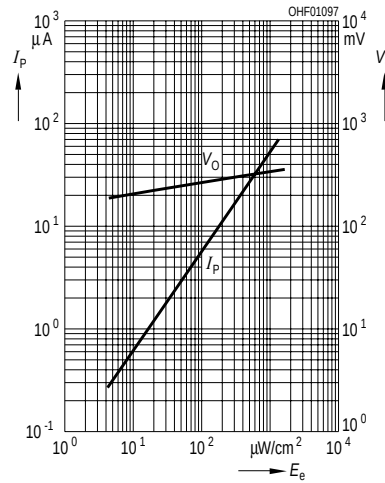
Characteristics (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Spektrale Fotoempfindlichkeit Spectral sensitivity	S_λ	0.63	AAW
Quantenausbeute Quantum yield	η	0.9	Electrons Photon
Leerlaufspannung, $E_e = 1\text{ mW/cm}^2$ Open-circuit voltage	V_O	350 (≥ 280)	mV
Kurzschlußstrom, $E_e = 1\text{ mW/cm}^2$ Short-circuit current	I_{SC}	56	μA
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent $R_L = 50\text{ }\Omega$; $V_R = 5\text{ V}$; $\lambda = 850\text{ nm}$; $I_p = 800\text{ }\mu\text{A}$	t_r, t_f	20	ns
Durchlaßspannung, $I_F = 100\text{ mA}$, $E = 0$ Forward voltage	V_F	1.3	V
Kapazität, $V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_0	72	pF
Temperaturkoeffizient von V_O Temperature coefficient of V_O	TC_{V_O}	- 2.6	mV/K
Temperaturkoeffizient von I_{SC} Temperature coefficient of I_{SC}	$TC_{I_{SC}}$	0.03	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 10\text{ V}$	NEP	4.0×10^{-14}	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 10\text{ V}$ Detection limit	D^*	6.6×10^{12}	$\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$

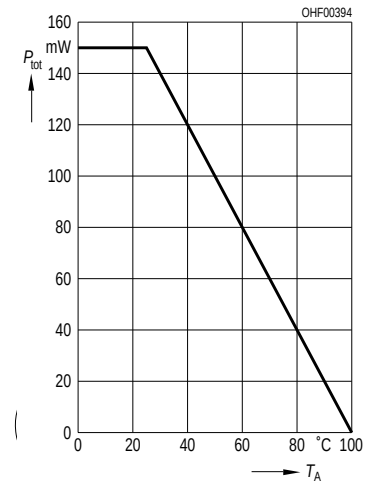
Relative Spectral Sensitivity
 $S_{\text{rel}} = f(\lambda)$



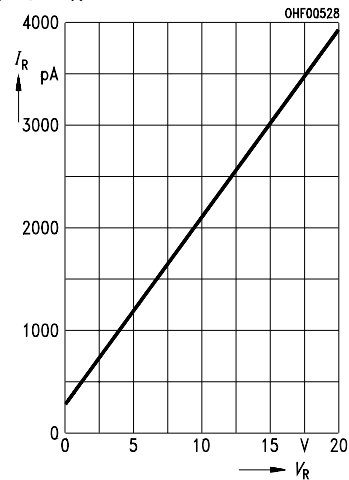
Photocurrent $I_P = f(E_e)$, $V_R = 5 \text{ V}$
Open-Circuit Voltage $V_O = f(E_e)$



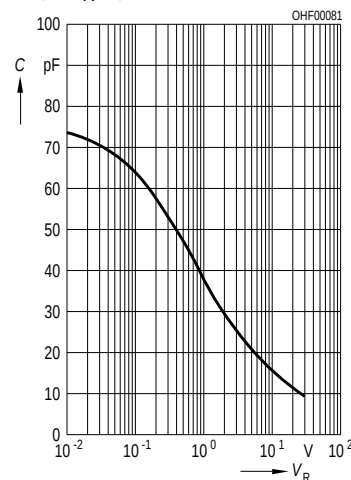
Total Power Dissipation
 $P_{\text{tot}} = f(T_A)$



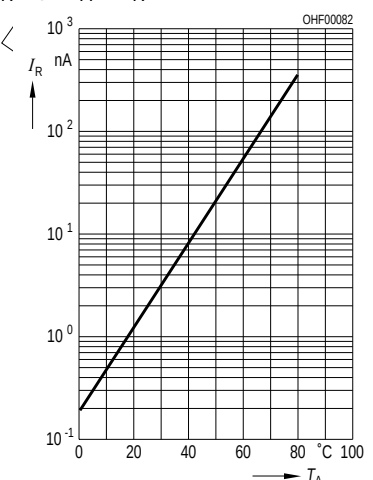
Dark Current
 $I_R = f(V_R)$, $E = 0$



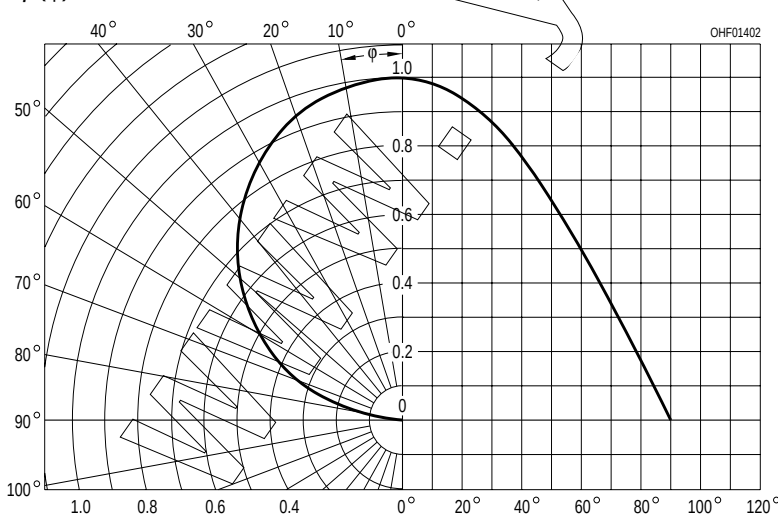
Capacitance
 $C = f(V_R)$, $f = 1 \text{ MHz}$, $E = 0$



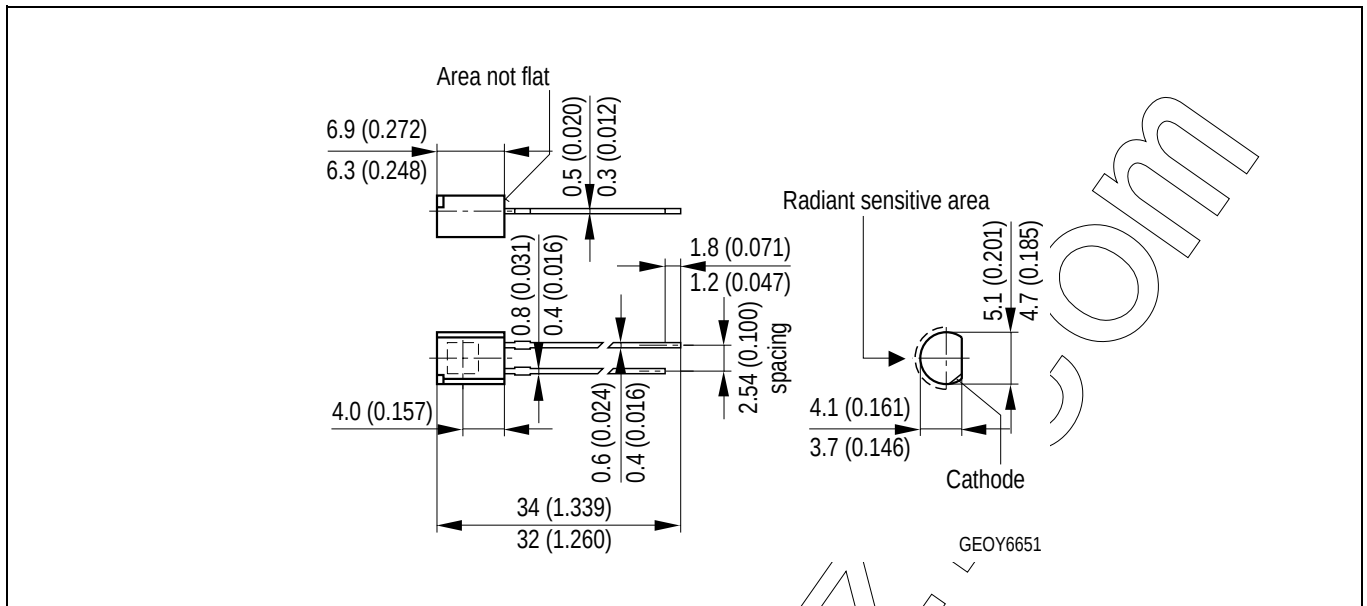
Dark Current
 $I_R = f(T_A)$, $V_R = 10 \text{ V}$, $E = 0$



Directional Characteristics
 $S_{\text{rel}} = f(\varphi)$



Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

Published by OSRAM Opto Semiconductors GmbH & Co. OHG
Wernerwerkstrasse 2, D-93049 Regensburg

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Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

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